

N-Channel 60 V (D-S) MOSFET



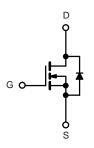
| PRODUCT SUMMARY | | | | |
|---------------------|--------------------------------|---------------------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (m Ω) | I _D (A) ^a | | |
| 60 | 6.9 at V _{GS} = 10 V | 70 | | |
| | 9.5 at V _{GS} = 4.5 V | 60 | | |

FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET

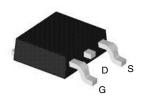
APPLICATIONS

• DC/DC converters



N-Channel MOSFET





Top View

| Parameter | | Symbol | Limit | Unit | |
|---|-------------------------|-----------------------------------|--|------|--|
| Gate-Source Voltage | | V _{GS} | ± 20 | V | |
| Continuous Drain Current (T _J = 175 °C) ^b | T _C = 25 °C | I- | 70 | | |
| | T _C = 100 °C | I _D | 65 ^a | | |
| Pulsed Drain Current | I _{DM} | 280 | А | | |
| Continuous Source Current (Diode Conduction) | Is | 70 ^a | | | |
| Avalanche Current | I _{AS} | 69 | | | |
| Single Avalanche Energy (Duty Cycle ≤ 1 %) | L = 0.1 mH | E _{AS} | 375 | mJ | |
| Maximum Power Dissipation | T _C = 25 °C | P _D | 186 | W | |
| Maximum Fower Dissipation | T _A = 25 °C | ' D | 3.5 ^b , 8.8 ^{b, c} | \ \v | |
| Operating Junction and Storage Temperature Range | <u>.</u> | T _J , T _{stg} | - 55 to 175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Marian and Irration to Ambianta | t ≤ 10 sec | R _{thJA} | 13 | 18 | | |
| Maximum Junction-to-Ambient ^a | Steady State | | 35 | 50 | °C/W | |
| Maximum Junction-to-Case | | R _{thJC} | 0.81 | 1.1 | | |

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s}$.

Rev. 1. 0





| SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted) Parameter Symbol Test Conditions Min. Typ. ^a Max. U | | | | | | Unit | |
|--|---------------------|---|---|----------|--------|-------|--|
| | Symbol | rest conditions | IVIIII. | тур." | IVIAA. | Offic | |
| Static Paris Common Paris I de la Vallence | 1 1/ | V 0.V.L 250A | 60 | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$ | | | | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | | 3 | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| | | V _{DS} = 48 V, V _{GS} = 0 V | | | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ | | | 50 μA | | |
| | | $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$ | | | 250 | | |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} = 5 V, V _{GS} = 10 V | 100 | | | Α | |
| Drain-Source On-State Resistance ^b | R _{DS(on)} | V _{GS} = 10 V, I _D = 10 A | _{SS} = 10 V, I _D = 10 A 6.9 | | 7.9 | | |
| | | V _{GS} = 4.5 V, I _D = 10 A | | 9.5 | 11.5 | mΩ | |
| Forward Transconductance ^b | 9 _{fs} | V _{DS} = 15 V, I _D = 10 A | | 65 | | S | |
| Dynamic | - | | | <u>'</u> | | | |
| Input Capacitance | C _{iss} | | | 1550 | | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$ | | 360 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 115 | | | |
| Total Gate Charge ^c | Q_g | | | 67 | 90 | | |
| Gate-Source Charge ^c | Q_{gs} | $V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$ | | 20 | | nC | |
| Gate-Drain Charge ^c | Q_{gd} | | | 15.5 | | | |
| Turn-On Delay Time ^c | t _{d(on)} | | | 11 | | - ns | |
| Rise Time ^c | t _r | $V_{DD} = 30 \text{ V, R}_{L} = 0.6 \Omega$ | | 16 | | | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ | | 35 | | | |
| Fall Time ^c | t _f | | | 20 | | | |
| Source-Drain Diode Ratings and Cha | aracteristics (| T _C = 25 °C) | | | | | |
| Pulsed Current | I _{SM} | | | | 280 | Α | |
| Diode Forward Voltage | V _{SD} | I _F = 10 A, V _{GS} = 0 V | | 1 | 1.5 | V | |
| Reverse Recovery Time | t _{rr} | I _F = 10 A, di/dt = 100 A/µs | | 45 | 100 | ns | |

Notes:

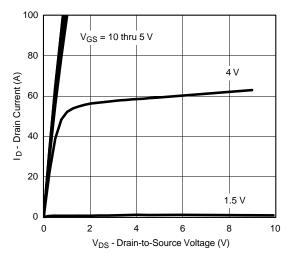
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

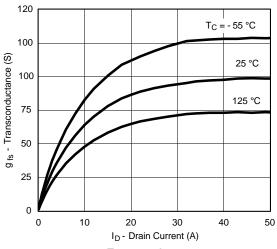




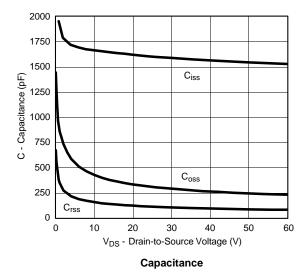
TYPICAL CHARACTERISTICS (25 °C unless noted)

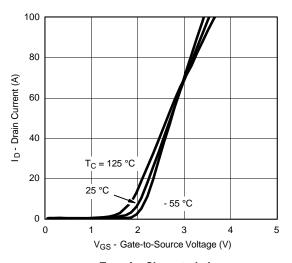


Output Characteristics

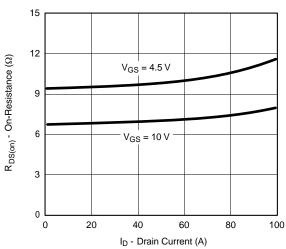


Transconductance

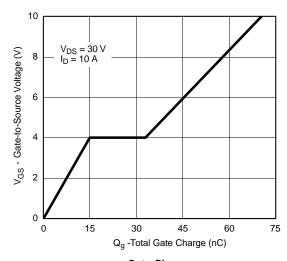




Transfer Characteristics



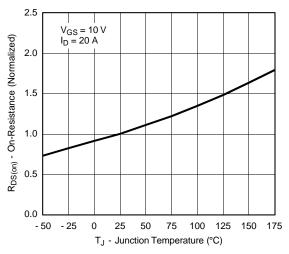
On-Resistance vs. Drain Current



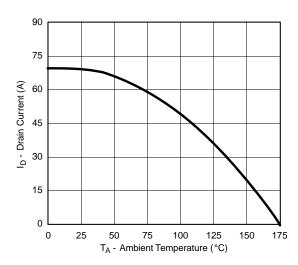
Gate Charge



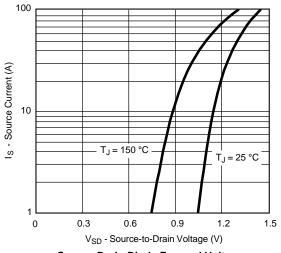
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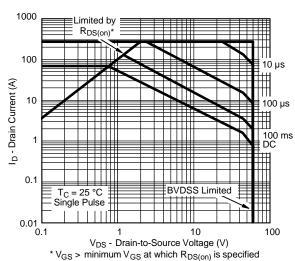
On-Resistance vs. Junction Temperature



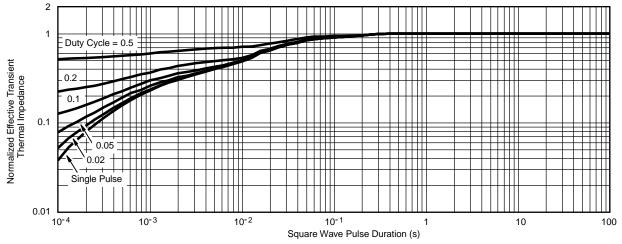
Maximum Drain Current vs. Ambient Temperature



Source-Drain Diode Forward Voltage

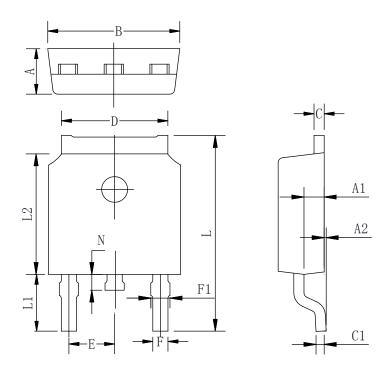


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252-2L PACKAGE OUTLINE



100 ms

COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| Symbol | Min | Тур | Max | |
|--------|-----------|------|-------|--|
| A | 2.10 | 2.30 | 2.50 | |
| A1 | 0.88 | 1.01 | 1.16 | |
| A2 | 0.00 | 0.15 | 0.28 | |
| В | 6.40 | 6.60 | 6.80 | |
| С | 0.42 | 0.50 | 0.63 | |
| C1 | 0.42 | 0.50 | 0.63 | |
| D | 5.08 | 5.32 | 5.65 | |
| Е | 2.286 TYP | | | |
| F | 0.63 | 0.76 | 0.89 | |
| F1 | 0.64 | 0.86 | 1.08 | |
| L | 9.30 | 9.90 | 10.80 | |
| L1 | 2.4 | 2.8 | 3.6 | |
| L2 | 5.90 | 6.10 | 6.55 | |
| N | 0.57 | 0.80 | 1.05 | |

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